

U.S. Patent Application Serial No. 10/041,609  
Amendment dated September 11, 2003  
Reply to OA of April 23, 2003

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1-17 (Canceled)

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8. (Currently amended): Semiconductor device having comprising:  
a semiconductor substrate having an underlying semiconductor surface;  
an insulator film deposited on said underlying semiconductor surface, said insulator film forming a  
semiconductor-insulator junction obtained by depositing an insulator film on an underlying semiconductor  
surface,

wherein the interfacial level density of said semiconductor-insulator junction is  $10^{12}$  eV<sup>-1</sup>cm<sup>-2</sup> or less  
as a result that, and

said insulator film is deposited on said underlying semiconductor surface after a treatment that  
reduces interfacial defects on said semiconductor-insulator junction utilizing a reaction of a treatment gas  
supplied with to the semiconductor substrate having said underlying semiconductor surface via a thermal  
catalysis body provided near said substrate.

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*✓* 19. (Previously presented): Semiconductor device as claimed in claim 18, wherein said semiconductor-insulation junction is one obtained by deposition of said insulator film, which is carried out in said same process chamber after said treatment and utilizes a reaction of a deposition gas supplied with said substrate via said same thermal catalysis body.